

isc Silicon NPN Power Transistors

BDT81F/83F/85F/87F

DESCRIPTION

- DC Current Gain $-h_{FE} = 40(\text{Min})@ I_C = 5A$
- Collector-Emitter Sustaining Voltage-
: $V_{CEO(\text{SUS})} = 60V(\text{Min})$ - BDT81F; 80V(Min)- BDT83F;
100V(Min)- BDT85F; 120V(Min)- BDT87F
- Complement to Type BDT82F/84F/86F/88F

APPLICATIONS

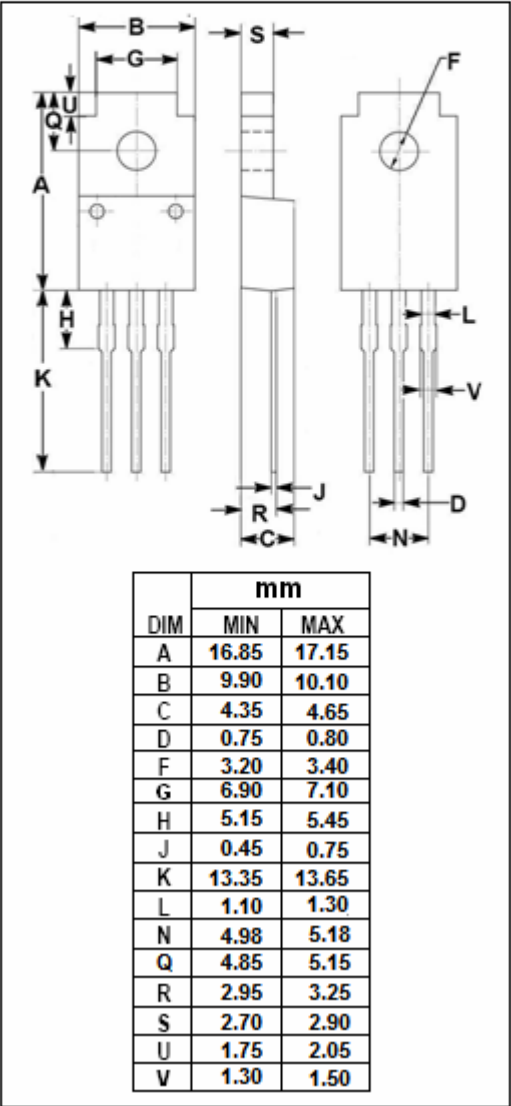
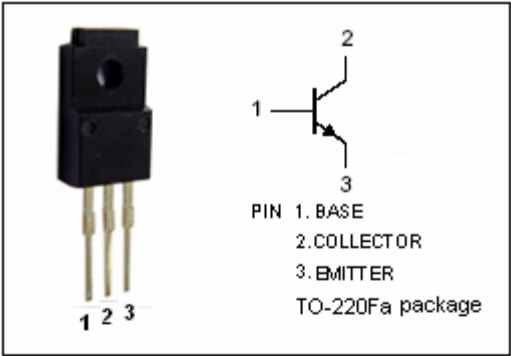
- Designed for use in audio output stages and general amplifier and switching applications

ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}\text{C}$)

SYMBOL	PARAMETER		VALUE	UNIT
V _{CBO}	Collector-Base Voltage	BDT81F	60	V
		BDT83F	80	
		BDT85F	100	
		BDT87F	120	
V _{CEO}	Collector-Emitter Voltage	BDT81F	60	V
		BDT83F	80	
		BDT85F	100	
		BDT87F	120	
V _{EBO}	Emitter-Base Voltage		7	V
I _C	Collector Current-Continuous		15	A
I _{CM}	Collector Current-Peak		20	A
I _B	Base Current		4	A
P _C	Collector Power Dissipation T _C =25℃		36	W
T _j	Junction Temperature		150	℃
T _{stg}	Storage Temperature Range		-65~150	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance,Junction to Case	6	$^{\circ}\text{C}/\text{W}$



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ELECTRICAL CHARACTERISTICS

 $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	BDT81F	$I_C=30\text{mA}; I_B=0$	60			V
		BDT83F		80			
		BDT85F		100			
		BDT87F		120			
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage		$I_C=5\text{A}; I_B=0.5\text{A}$			1.0	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage		$I_C=7\text{A}; I_B=0.7\text{A}$			1.6	V
$V_{BE(on)}$	Base-Emitter On Voltage		$I_C=5\text{A}; V_{CE}=4\text{V}$			1.5	V
I_{CES}	Collector Cutoff Current		$V_{CE}=0.8V_{CB0max}; V_{BE}=0$			1	mA
I_{CBO}	Collector Cutoff Current		$V_{CB}=V_{CB0max}; I_E=0$			0.2	mA
I_{EBO}	Emitter Cutoff Current		$V_{EB}=7\text{V}; I_C=0$			0.1	mA
h_{FE-1}	DC Current Gain		$I_C=50\text{mA}; V_{CE}=10\text{V}$	40			
h_{FE-2}	DC Current Gain		$I_C=5\text{A}; V_{CE}=4\text{V}$	40			
f_T	Current-Gain—Bandwidth Product		$I_C=0.5\text{A}; V_{CE}=10\text{V}$		10		MHz

Switching Times

t_{on}	Turn-On Time	$I_C=7\text{A}; I_{B1}=-I_{B2}=0.7\text{A}$			1	μs
t_{off}	Turn-Off Time				2	μs